

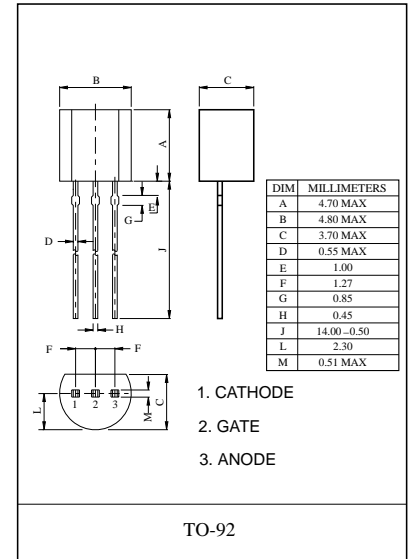
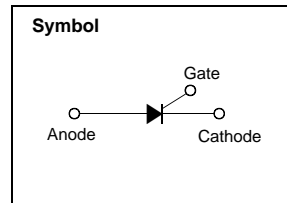
Silicon Planar PNP Thyristor

MAIN FEATURES

Symbol	Value	Unit	
$I_{T(RMS)}$	0.8	A	
V_{DRM}/V_{RRM}	MCR100-6/F	400	V
	MCR100-8/F	600	
T_J	Junction Temperature	-40 to 125	°C
T_{stg}	Storage Temperature	-55 to 150	°C

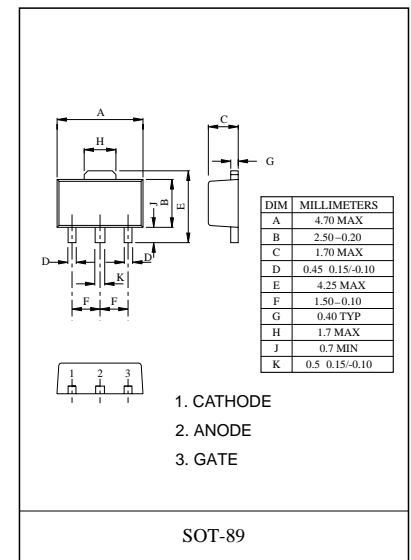
DESCRIPTION

Logic level sensitive gate triac intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.



FEATURES

- Blocking voltage to 400 V (MCR100-6/F) , 600V (MCR100-8/F)
- RMS on-state current to 0.8 A
- General purpose switching



APPLICATIONS

- General purpose switching
- Phase control applications
- Solid state relays.

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT	
On state voltage *	V_{TM}	$I_{TM}=1A$		1.7	V	
Gate trigger voltage	V_{GT}	$V_{AK}=7V$		0.8	V	
Peak Repetitive forward and reverse blocking voltage	V_{DRM} AND V_{RRM}	$I_{DRM}= 10 \mu A$	400 600		V	
Peak forward or reverse blocking current	I_{DRM} I_{RRM}	$V_{AK}= \text{Rated}$ V_{DRM} or V_{RRM}		10	μA	
Holding current	I_H	$I_{HL}=20mA, V_{AK}=7V$		5	mA	
Gate trigger current	I_{GT}	$V_{AK}=7V$	A2	5	25	μA
			A1	15	30	μA
			A	20	100	μA
			B	80	200	μA

* Forward current applied for 1 ms maximum duration, duty cycle $\leq 1\%$.

Typical Characteristics

